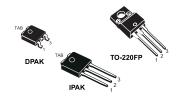
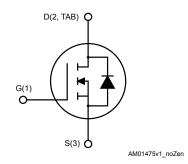


Datasheet

# N-channel 600 V, 0.8 Ω typ., 5 A MDmesh™ II Power MOSFETs in DPAK, TO-220FP and IPAK packages





#### **Features**

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	l <sub>D</sub>	Package	
STD7NM60N	600 V	600 V 0.9 Ω 5 A			DPAK
STF7NM60N			TO-220FP		
STU7NM60N				IPAK	

- 100% avalanche tested
- · Low input capacitance and gate charge
- · Low gate input resistance

#### **Applications**

· Switching applications

#### **Description**

These devices are N-channel Power MOSFETs developed using the second generation of MDmesh™ technology. These revolutionary Power MOSFETs associate a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. They are therefore suitable for the most demanding high-efficiency converters.

Product status link				
STD7NM60N				
STF7NM60N				
STU7NM60N				



### 1 Electrical ratings

Table 1. Absolute maximum ratings

Complete	Davissa	Va	llue	11:4
Symbol	Parameter	DPAK, IPAK	TO-220FP	- Unit
$V_{DS}$	Drain-source voltage	600		V
V <sub>GS</sub>	Gate-source voltage	Gate-source voltage ±25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C 5		5 (1)	А
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C 3 3 (1)		3 (1)	А
I <sub>DM</sub> (2)	Drain current (pulsed)	20	20 (1)	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	45	20	W
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat-sink (t = 1 s, T <sub>C</sub> = 25 °C)			kV
dv/dt (3)	Peak diode recovery voltage slope	15		V/ns
T <sub>j</sub>	Operating junction temperature range -55 to 150		°C	
T <sub>stg</sub>	Storage temperature range	-55 (	0 150	-0

- 1. Limited by maximum junction temperature.
- 2. Pulse width limited by safe operating area.
- 3.  $I_{SD} \le 5$  A,  $di/dt \le 100$  A/ $\mu$ s,  $V_{DSpeak} \le V_{(BR)DSS}$ ,  $V_{DD} = 80\%$   $V_{(BR)DSS}$ .

Table 2. Thermal data

Symbol	Parameter	Value			Unit
Symbol	r al allietei	DPAK	TO-220FP	IPAK	Oilit
R <sub>thj-case</sub>	Thermal resistance junction-case	2.78	6.25	2.78	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient		62.5	100	°C/W
R <sub>thj-pcb</sub> <sup>(1)</sup>	Thermal resistance junction-pcb	50			°C/W

<sup>1.</sup> When mounted on 1inch<sup>2</sup> FR-4 board, 2 oz Cu.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I <sub>AS</sub> <sup>(1)</sup>	Avalanche current, repetitive or not-repetitive	2	Α
E <sub>AS</sub> <sup>(2)</sup>	Single pulse avalanche energy	119	mJ

- 1. Pulse width limited by  $T_j$  max.
- 2. Starting  $T_j = 25$  °C,  $I_D = I_{AS}$ ,  $V_{DD} = 50$  V.

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#### 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	600			V
Zero gate voltage drain	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 600 V			1	μA	
IDSS	I <sub>DSS</sub> current	$V_{GS}$ = 0 V, $V_{DS}$ = 600 V, $T_{C}$ = 125 °C <sup>(1)</sup>			100	μA
I <sub>GSS</sub>	Gate body leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A		0.8	0.9	Ω

<sup>1.</sup> Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance			363		
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 50 V, f = 1 MHz, V <sub>GS</sub> = 0 V	_	24.6	1 _	pF
C <sub>rss</sub>	Reverse transfer capacitance			1.1		
Coss eq. (1)	Equivalent capacitance time related	V <sub>DS</sub> = 0 to 480 V, V <sub>GS</sub> = 0 V	-	130	-	pF
$R_{G}$	Intrinsic gate resistance	f = 1 MHz open drain	-	5.4	-	Ω
Qg	Total gate charge	V <sub>DD</sub> = 480 V, I <sub>D</sub> = 5 A, V <sub>GS</sub> = 0 to 10 V		14		
Q <sub>gs</sub>	Gate-source charge	(see Figure 14. Test circuit for gate charge	-	2.7	_	nC
Q <sub>gd</sub>	Gate-drain charge	behavior)		7.7		

<sup>1.</sup>  $C_{\text{oss eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{\text{oss}}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 2.5 A,		7		
t <sub>r</sub>	Rise time	$R_G = 4.7 \Omega$ , $V_{GS} = 10 V$		10		
t <sub>d(off)</sub>	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching	-	26	-	ns
t <sub>f</sub>	Fall time	time waveform)		12		

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Table 7. Source drain diode

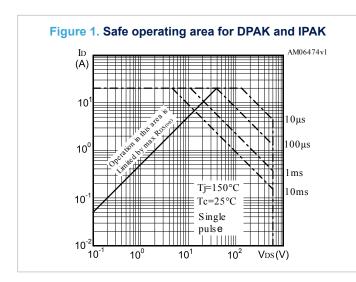
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>SD</sub>	Source-drain current				5	
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)		-		20	Α
V <sub>SD</sub> (2)	Forward on voltage	I <sub>SD</sub> = 5 A, V <sub>GS</sub> = 0 V	-		1.3	V
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 5 A, di/dt = 100 A/μs		213		ns
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DD</sub> = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery	-	1.5		μC
I <sub>RRM</sub>	Reverse recovery current	times)		14		Α
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 5 A, di/dt = 100 A/μs		265		ns
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DD</sub> = 60 V, T <sub>j</sub> = 150 °C(see Figure 15. Test circuit for inductive load switching and	-	1.8		μC
I <sub>RRM</sub>	Reverse recovery current	diode recovery times)		14		Α

<sup>1.</sup> Pulse width limited by safe operating area.

<sup>2.</sup> Pulsed: pulse duration =  $300 \mu s$ , duty cycle 1.5%.



#### 2.1 Electrical characteristics curves



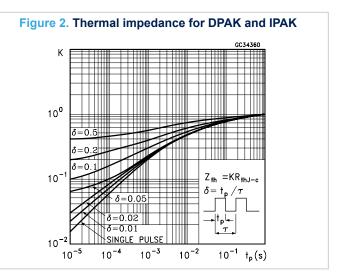
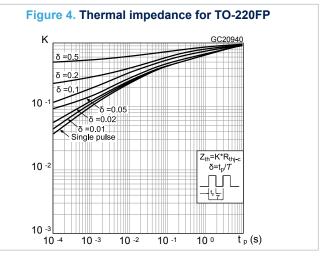
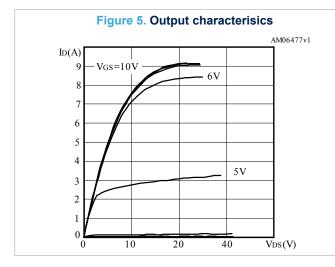
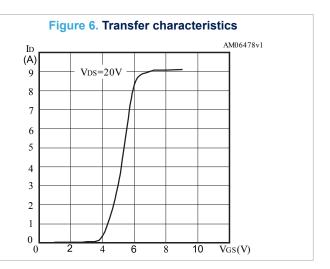


Figure 3. Safe operating area for TO-220FP AM06475v1 ID (A) 10 10µs 100 µs 100 1ms 10ms Tj=150°C 10-Tc=25°C Single pulse 10-2 10-1 10¹ 10<sup>2</sup>







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Figure 7. Gate charge vs gate-source voltage

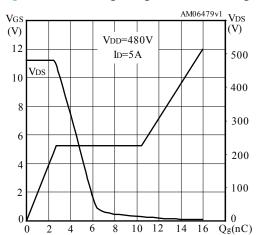


Figure 8. Static drain-source on-resistance

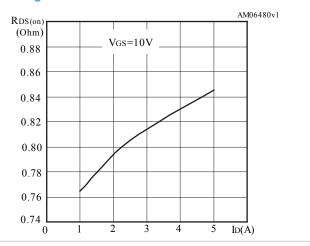


Figure 9. Capacitance variations

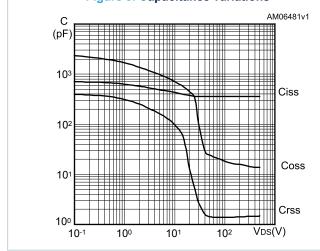


Figure 10. Normalized gate threshold voltage vs temperature

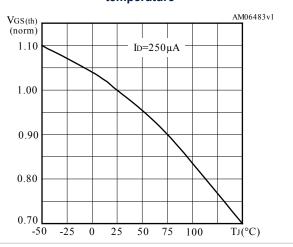


Figure 11. Normalized on-resistance vs temperature

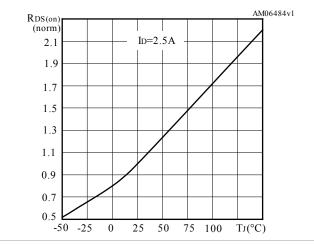
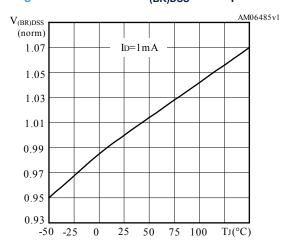


Figure 12. Normalized V<sub>(BR)DSS</sub> vs temperature



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#### 3 Test circuits

Figure 13. Test circuit for resistive load switching times

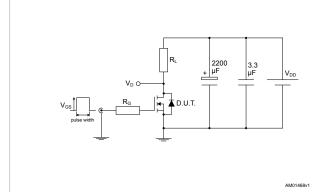


Figure 14. Test circuit for gate charge behavior

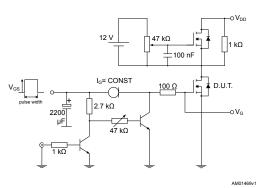


Figure 15. Test circuit for inductive load switching and diode recovery times

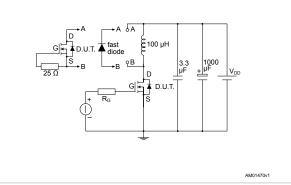


Figure 16. Unclamped inductive load test circuit

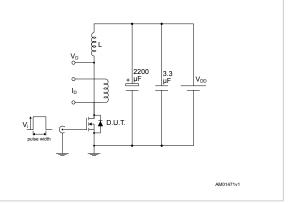


Figure 17. Unclamped inductive waveform

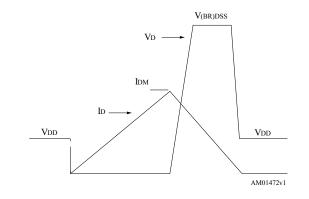
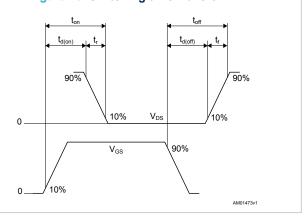


Figure 18. Switching time waveform



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## 4 Package information

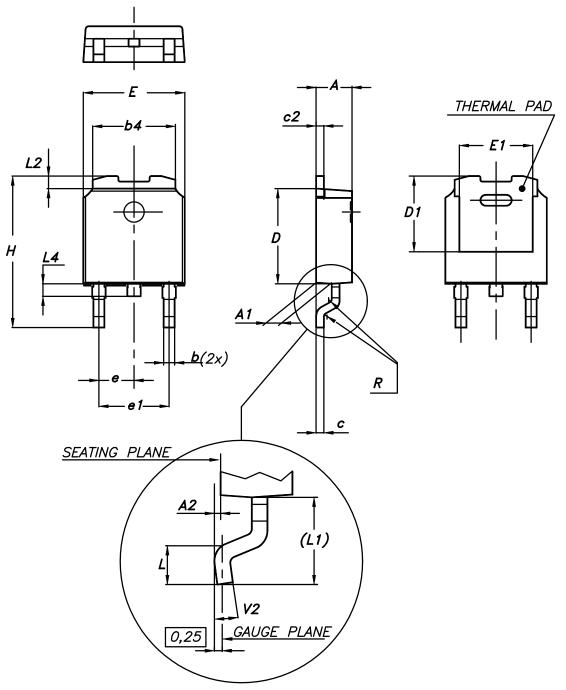
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

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#### 4.1 DPAK (TO-252) type A package information

Figure 19. DPAK (TO-252) type A package outline



0068772\_A\_25



Table 8. DPAK (TO-252) type A mechanical data

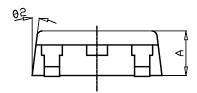
Dim		mm					
Dim.	Min.	Тур.	Max.				
А	2.20		2.40				
A1	0.90		1.10				
A2	0.03		0.23				
b	0.64		0.90				
b4	5.20		5.40				
С	0.45		0.60				
c2	0.48		0.60				
D	6.00		6.20				
D1	4.95	5.10	5.25				
Е	6.40		6.60				
E1	4.60	4.70	4.80				
е	2.159	2.286	2.413				
e1	4.445	4.572	4.699				
Н	9.35		10.10				
L	1.00		1.50				
(L1)	2.60	2.80	3.00				
L2	0.65	0.80	0.95				
L4	0.60		1.00				
R		0.20					
V2	0°		8°				

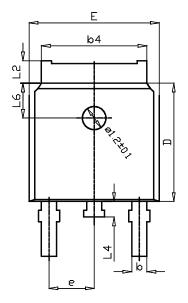
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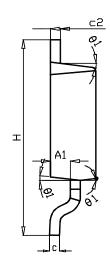


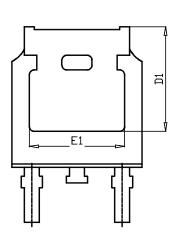
### 4.2 DPAK (TO-252) type C package information

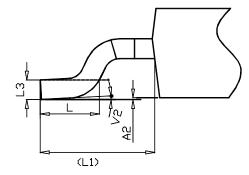
Figure 20. DPAK (TO-252) type C package outline











0068772\_C\_25



Table 9. DPAK (TO-252) type C mechanical data

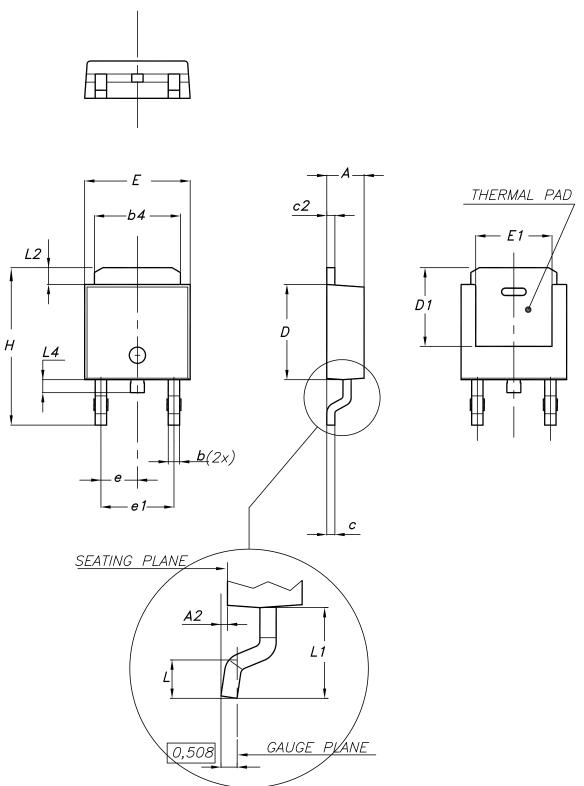
Dim.		mm	
DIM.	Min.	Тур.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
С	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
Е	6.50	6.60	6.70
E1	4.70		
е	2.186	2.286	2.386
Н	9.80	10.10	10.40
L	1.40	1.50	1.70
L1		2.90 REF	·
L2	0.90		1.25
L3		0.51 BSC	
L4	0.60	0.80	1.00
L6		1.80 BSC	
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

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#### 4.3 DPAK (TO-252) type E package information

Figure 21. DPAK (TO-252) type E package outline



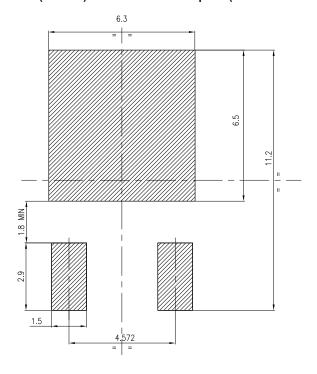
0068772\_type-E\_rev.25



Table 10. DPAK (TO-252) type E mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
С	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
е		2.286	
e1		4.572	
Н	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 22. DPAK (TO-252) recommended footprint (dimensions are in mm)

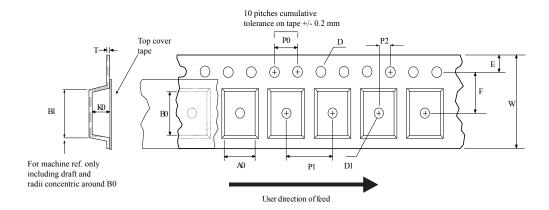


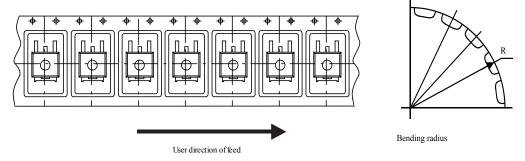
FP\_0068772\_25



#### 4.4 DPAK (TO-252) packing information

Figure 23. DPAK (TO-252) tape outline





AM08852v1

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A 40mm min. access hole at slot location

Tape slot in core for tape start

Full radius

Tape start

tape start 2.5mm min.width

Figure 24. DPAK (TO-252) reel outline

AM06038v1

Table 11. DPAK (TO-252) tape and reel mechanical data

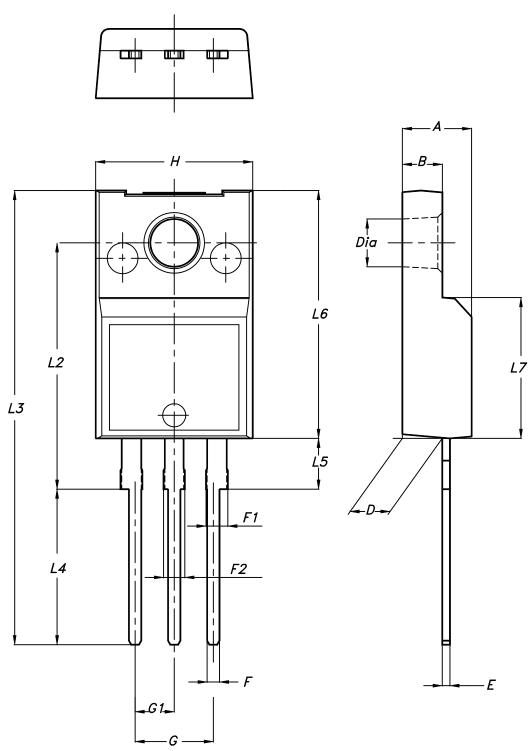
Таре			Reel		
Dim.	mm		Dim	mm	
Dilli.	Min.	Max.	Max. Dim. Min.	Min.	Max.
A0	6.8	7	Α		330
В0	10.4	10.6	В	1.5	
B1		12.1	С	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
Е	1.65	1.85	N	50	
F	7.4	7.6	Т		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base	qty.	2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
Т	0.25	0.35			
W	15.7	16.3			

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### 4.5 TO-220FP package information

Figure 25. TO-220FP package outline



7012510\_Rev\_12\_B



Table 12. TO-220FP package mechanical data

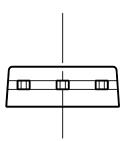
Dim.		mm	
Dilli.	Min.	Тур.	Max.
А	4.4		4.6
В	2.5		2.7
D	2.5		2.75
Е	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
Н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

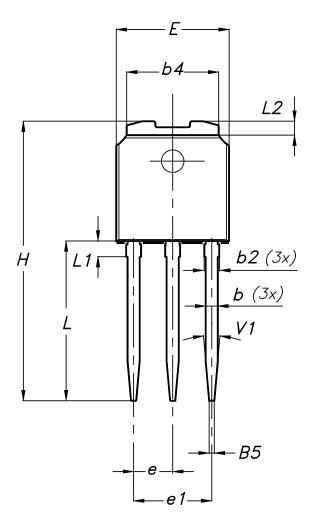
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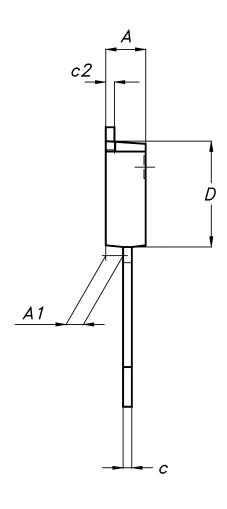


#### IPAK (TO-251) type A package information 4.6

Figure 26. IPAK (TO-251) type A package outline







0068771\_IK\_typeA\_rev14

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Table 13. IPAK (TO-251) type A package mechanical data

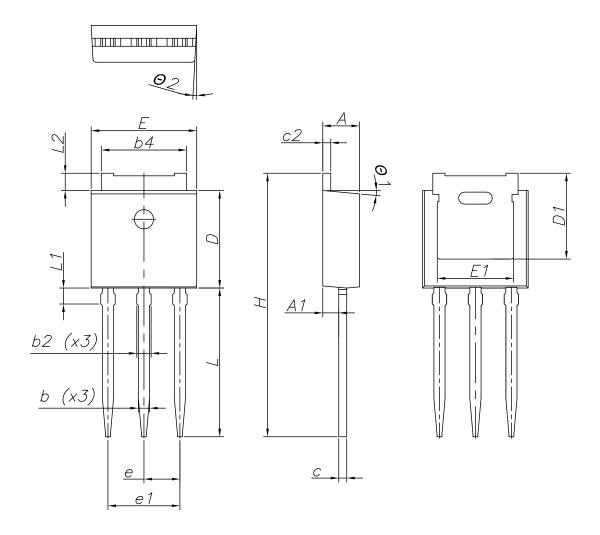
Dim.		mm	
Dim.	Min.	Тур.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
е		2.28	
e1	4.40		4.60
Н		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

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### 4.7 IPAK (TO-251) type C package information

Figure 27. IPAK (TO-251) type C package outline



0068771\_IK\_typeC\_rev14

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Downloaded from Arrow.com.



Table 14. IPAK (TO-251) type C package mechanical data

Dim.		mm	
DIM.	Min.	Тур.	Max.
А	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
С	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
е	2.20	2.25	2.30
e1	4.40	4.50	4.60
Н	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

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# 5 Ordering information

Table 15. Order codes

Order code	Marking	Package	Packing
STD7NM60N		DPAK	Tape and reel
STF7NM60N	7NM60N	TO-220FP	Tube
STU7NM60N		IPAK	Tube

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### **Revision history**

**Table 16. Document revision history** 

Date	Version	Changes
29-Oct-2009	1	First release.
19-Jul-2010	2	Corrected values in Table 3: Thermal data.
11-Oct-2010	3	Inserted new value in Table 6: Dynamic
04-Nov-2010		Changed R <sub>DS(on)</sub> typical value.
		The part number STP7NM60N has been moved to a separate datasheet.
		Removed maturity status indication from cover page. The document status is production data.
05-Sep-2018		Updated title and features in cover page.
		Updated Section 1 Electrical ratings, Section 2 Electrical characteristics and Section 4 Package information.
		Minor text changes.

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